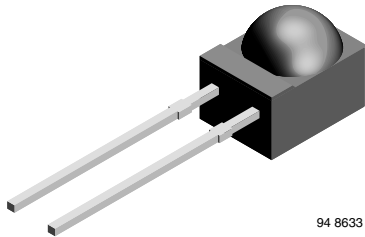


Silicon PIN Photodiode, RoHS Compliant



FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (in mm): 4.5 x 5 x 6
- Radiant sensitive area (in mm²): 7.5
- High radiant sensitivity
- Daylight blocking filter matched with 940 nm emitters
- Fast response times
- Angle of half sensitivity: $\phi = \pm 60^\circ$
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

DESCRIPTION

BPV22F is a PIN photodiode with high speed and high radiant sensitivity in a black, plastic package with side view lens and daylight blocking filter. Filter bandwidth is matched with 900 nm to 950 nm IR emitters. The lens achieves 80 % of sensitivity improvement in comparison with flat package.

APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmission systems, e.g. in combination with TSALxxxx series IR emitters

PRODUCT SUMMARY			
COMPONENT	I_{ra} (μA)	ϕ (deg)	$\lambda_{0.5}$ (nm)
BPV22F	80	± 60	870 to 1050

Note

Test condition see table “Basic Characteristics”

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPV22F	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	Side view

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	60	V
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_V	215	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 100	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5\text{ s}$	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R_{thJA}	350	K/W

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified



BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1	1.3	V
Breakdown voltage	$I_R = 100 \text{ }\mu\text{A}, E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10 \text{ V}, E = 0$	I_{ro}		2	30	nA
Diode capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_D		70		pF
Serial resistance	$V_R = 12 \text{ V}, f = 1 \text{ MHz}$	R_S		400		Ω
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	V_o		370		mV
Temperature coefficient of V_o	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK_{V_o}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	I_k		75		μA
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 5 \text{ V}$	I_{ra}	55	80		μA
Temperature coefficient of I_{ra}	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 10 \text{ V}$	$TK_{I_{ra}}$		0.1		%/K
Absolute spectral sensitivity	$V_R = 5 \text{ V}, \lambda = 870 \text{ nm}$	$s(\lambda)$		0.35		A/W
	$V_R = 5 \text{ V}, \lambda = 950 \text{ nm}$	$s(\lambda)$		0.6		A/W
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		λ_p		950		nm
Range of spectral bandwidth		$\lambda_{0.5}$		870 to 1050		nm
Quantum efficiency	$\lambda = 950 \text{ nm}$	η		90		%
Noise equivalent power	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		4×10^{-14}		W/ $\sqrt{\text{Hz}}$
Detectivity	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	D^*		6×10^{12}		$\text{cm}^2\sqrt{\text{Hz/W}}$
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t_r		100		ns
Fall time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t_f		100		ns
Cut-off frequency	$V_R = 12 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 870 \text{ nm}$	f_c		4		MHz
	$V_R = 12 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 950 \text{ nm}$	f_c		1		MHz

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

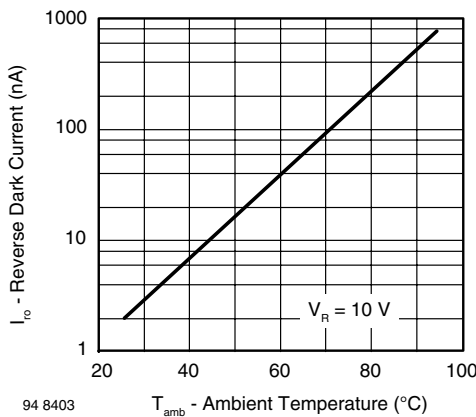


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

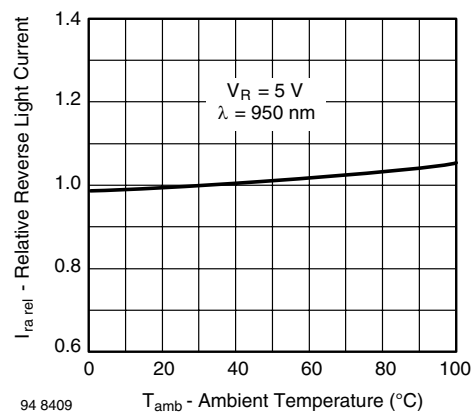
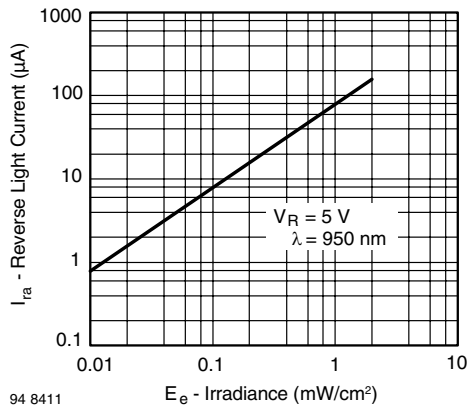
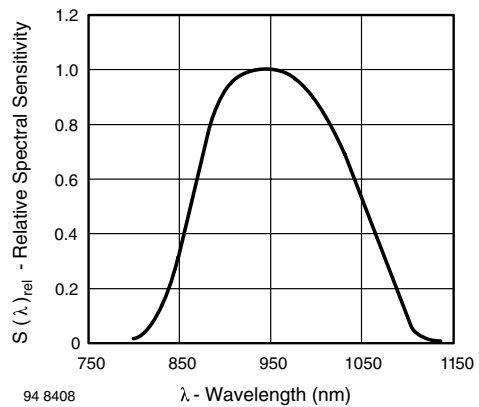


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



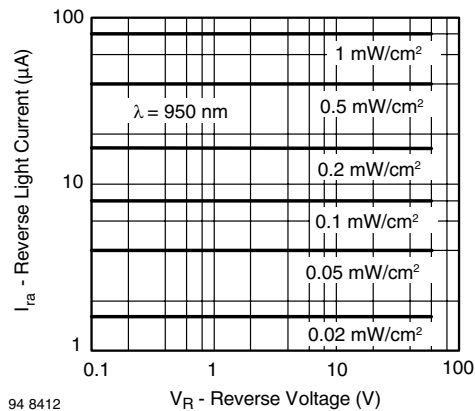
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Fig. 3 - Reverse Light Current vs. Irradiance



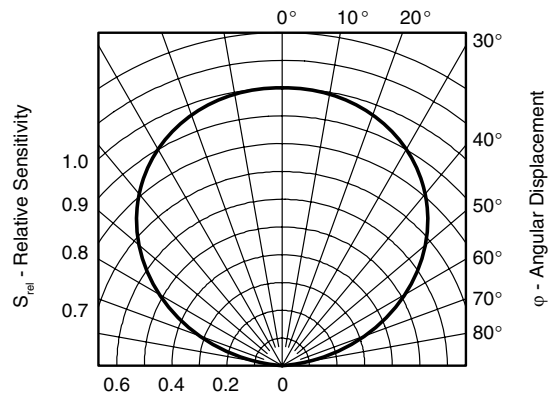
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Fig. 6 - Relative Spectral Sensitivity vs. Wavelength



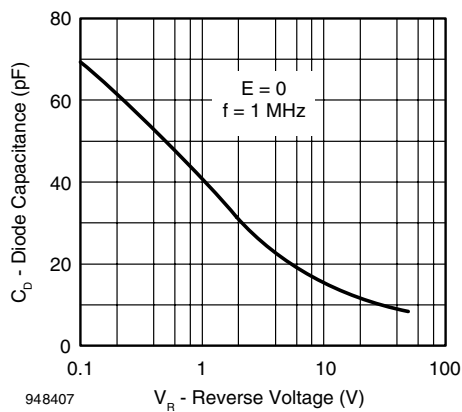
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Fig. 4 - Reverse Light Current vs. Reverse Voltage



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Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

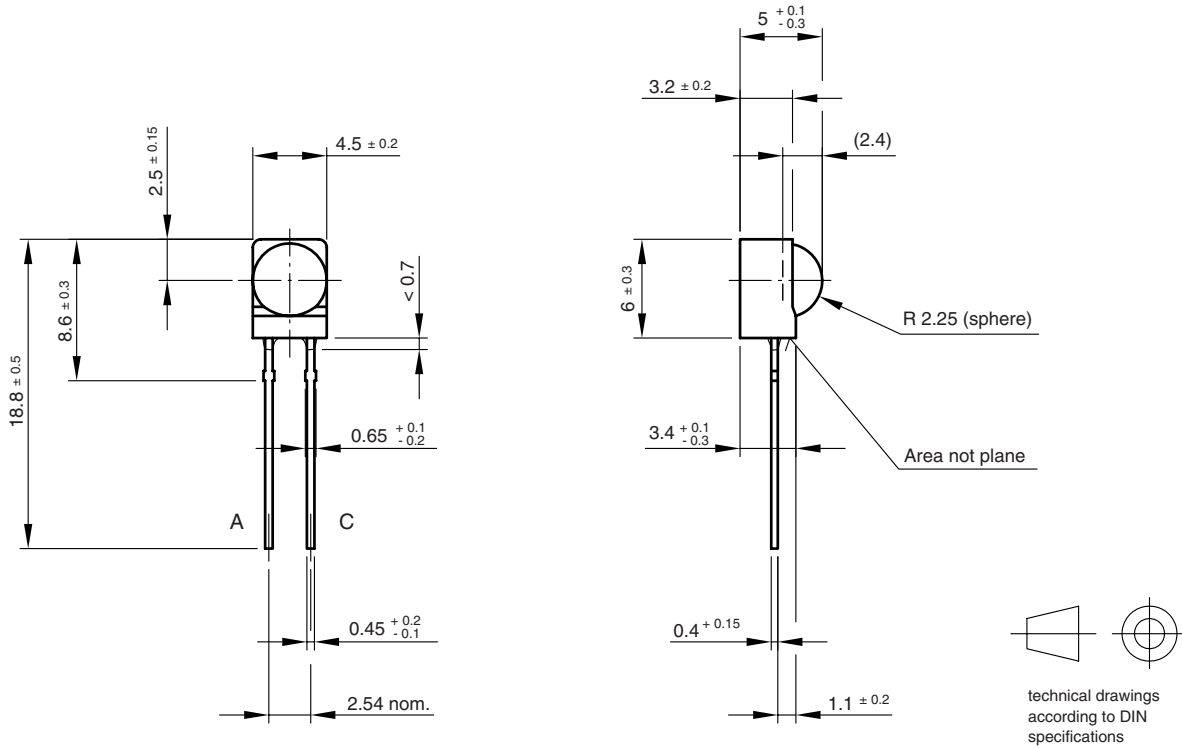


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Fig. 5 - Diode Capacitance vs. Reverse Voltage



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5199.01-4
Issue: 2; 19.06.01
95 11475



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